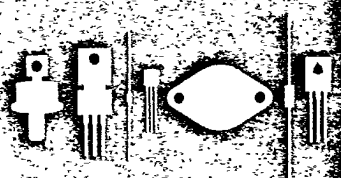


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145 Adams Avenue
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PN5033

P-CHANNEL JFET

JEDEC TO-92 CASE (DSG)

DESCRIPTION

The CENTRAL SEMICONDUCTOR PN5033 type is a silicon P-channel junction field effect transistor designed for low level amplifier applications.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL		UNIT
Drain-Gate Voltage	V _{DG}	20	V
Drain-Source Voltage	V _{DS}	20	V
Reverse Gate-Source Voltage	V _{GSR}	20	V
Gate Current	I _G	50	mA
Power Dissipation	P _D	200	mW
Operating and Storage Junction Temperature	T _J , T _{STG}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I _{GSS}	V _{GS} =15V		10	nA
I _{GSS}	V _{GS} =15V, T _A =100°C		0.5	μA
I _{DSS}	V _{DS} =10V	0.3	3.5	mA
BV _{GSS}	I _G =10μA	20		V
V _{GS}	V _{DS} =10V, I _D =0.03mA		2.3	V
V _{GS(OFF)}	V _{DS} =10V, I _D =1.0μA	0.3	2.5	V
Y _{fs}	V _{DS} =10V, V _{GS} =0, f=1.0kHz	1000	5000	μmho
Y _{os}	V _{DS} =10V, V _{GS} =0, f=1.0kHz		20	μmho
Re(y _{fs})	V _{DS} =10V, V _{GS} =0, f=1.0MHz	900		μmho
C _{iss}	V _{DS} =10V, V _{GS} =0, f=1.0MHz		25	pF
C _{rss}	V _{DS} =10V, V _{GS} =0, f=1.0MHz		7.0	pF
r _{ds(ON)}	V _{GS} =0, I _D =0, f=1.0kHz		1300	Ω
NF	V _{DS} =10V, V _{GS} =0, R _G =1.0MΩ, f=1.0kHz, BW=150Hz		2.0	dB
eN	V _{DS} =10V, V _{GS} =0, BW=150Hz		0.1	μV/√Hz

LEAD CODE:

1. DRAIN
2. SOURCE
3. GATE

